

Supplementary Information

Revealing and Engineering Contact-Origin Noise in Ultrathin Tellurium Transistors

Hae-Won Lee^a, Minjae Kim^b, Junho Ban^c, Jae Hyeon Jun^b, Kiyung Kim^b, Useok Choi^c, Jung Tae Lee^c and Byoung Hun Lee^{a,b,c}*

^aDepartment of Electrical Engineering, Pohang University of Science and Technology,
Cheongam-ro 77, Nam-gu, Pohang, Gyeongbuk 37673, Republic of Korea

^bNational Institute for Nanomaterials Technology, Pohang University of Science and
Technology, Cheongam-ro 77, Nam-gu, Pohang, Gyeongbuk 37673, Republic of Korea

^cGraduate School of Semiconductor Technology, Pohang University of Science and Technology,
Cheongam-ro 77, Nam-gu, Pohang, Gyeongbuk 37673, Republic of Korea

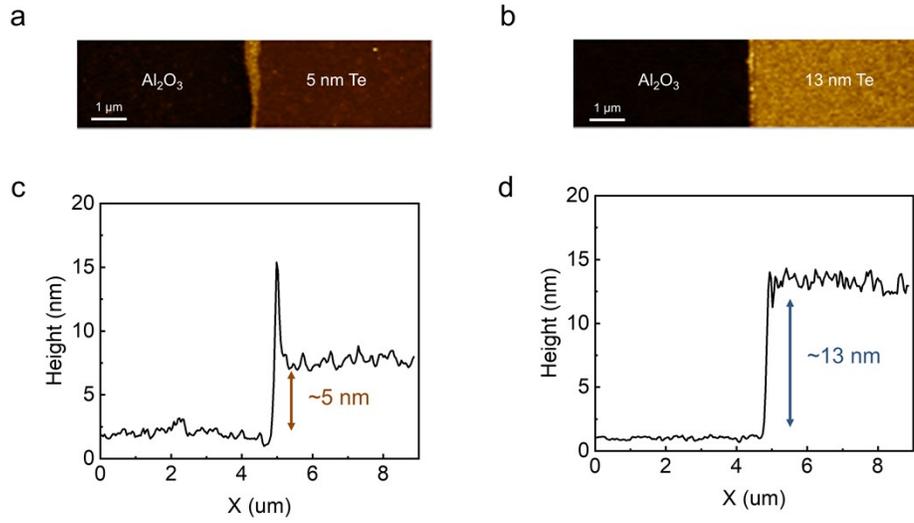


Fig. S1 Structural characterization of Te thin films via AFM. AFM topography images measured across the $\text{Al}_2\text{O}_3/\text{Te}$ step edge for (a) 5 nm and (b) 13 nm Te films (scale bar: 1 μm). Corresponding height line profiles extracted from the AFM images, confirming step heights of (c) 5 nm and (d) 13 nm, respectively, which correspond to the actual channel thicknesses.